

General Description

The WSP4065 is the highest performance trench N-ch and P-ch MOSFET with extreme high cell density, which provide excellent RDS(on) and gate charge for most of the synchronous buck converter applications.

The WSP4065 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

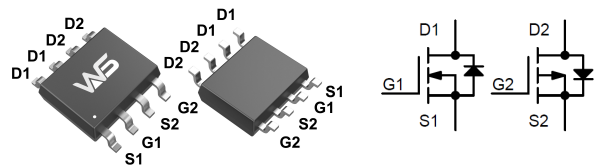
Product Summary

BVDSS	RDS(on)	ID
40V	16mΩ	10A
-40V	35mΩ	-10A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter.
- Networking DC-DC Power System
- Load Switch

SOP-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V _{DS}	Drain-Source Voltage	40	-40	V
V _{GS}	Gate-Source Voltage	±20	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	10	-10	A
I _D @T _C =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	4.8	-4.8	A
I _{DM}	Pulsed Drain Current ²	30	-30	A
EAS	Single Pulse Avalanche Energy ³	28	28	mJ
I _{AS}	Avalanche Current	11	11	A
P _D @T _C =25°C	Total Power Dissipation ⁴	2	2	W
T _{STG}	Storage Temperature Range	-55 to 150	-55 to 150	°C
T _J	Operating Junction Temperature Range	150	150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient (t < 10s)	---	62.5	°C/W
R _{θJA}	Thermal Resistance Junction-Ambient (Steady State)	---	80	°C/W

N-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	40	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.067	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =6A	---	16	18	mΩ
		V _{GS} =4.5V, I _D =5A	---	20	22	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.5	1.9	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.24	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =32V, V _{GS} =0V, T _J =85°C	---	---	1	uA
		V _{DS} =32V, V _{GS} =0V, T _J =85°C	---	---	30	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =8A	---	25	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.5	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =20V, V _{GS} =10V, I _D =6A	---	19	25	nC
Q _{gs}	Gate-Source Charge		---	4.5	---	
Q _{gd}	Gate-Drain Charge		---	4.8	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =20V, V _{GS} =10V, R _G =6Ω, I _D =1A, R _L =20Ω	---	8.5	---	ns
T _r	Rise Time		---	7.2	---	
T _{d(off)}	Turn-Off Delay Time		---	24	---	
T _f	Fall Time		---	5.3	---	
C _{iss}	Input Capacitance	V _{DS} =20V, V _{GS} =0V, f=1MHz	---	915	---	pF
C _{oss}	Output Capacitance		---	98	---	
C _{rss}	Reverse Transfer Capacitance		---	85	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	10	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	30	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =6A, T _J =25°C	---	---	1.1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper,t<10sec.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=11A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

P-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-40	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.03	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-5.0A$	---	35	39	$m\Omega$
		$V_{GS}=-4.5V, I_D=-4A$	---	40	50	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.3	-1.8	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.56	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-32V, V_{GS}=0V, T_J=85^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-32V, V_{GS}=0V, T_J=85^\circ\text{C}$	---	---	-30	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=-5V, I_D=-4A$	---	15	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	8	---	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-20V, V_{GS}=-10V, I_D=-5.0A$	---	18	---	nC
Q_{gs}	Gate-Source Charge		---	4.8	---	
Q_{gd}	Gate-Drain Charge		---	6.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-20V, V_{GS}=-10V, R_G=6\Omega, I_D=-1A, R_L=20\Omega.$	---	8.7	---	ns
T_r	Rise Time		---	7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	31	---	
T_f	Fall Time		---	17	---	
C_{iss}	Input Capacitance	$V_{DS}=-20V, V_{GS}=0V, f=1\text{MHz}$	---	1105	---	pF
C_{oss}	Output Capacitance		---	105	---	
C_{rss}	Reverse Transfer Capacitance		---	95	---	

Diode Characteristics

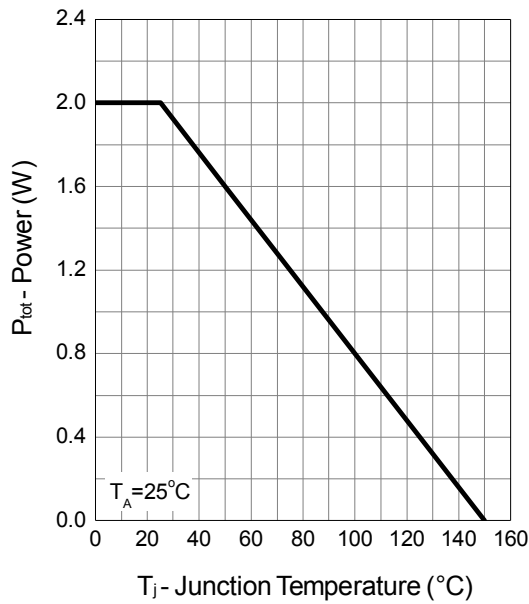
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,6}	$V_G=V_D=0V$, Force Current	---	---	-10	A
I_{SM}	Pulsed Source Current ^{2,6}		---	---	-30	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-5A, T_J=25^\circ\text{C}$	---	---	-1.1	V

Note :

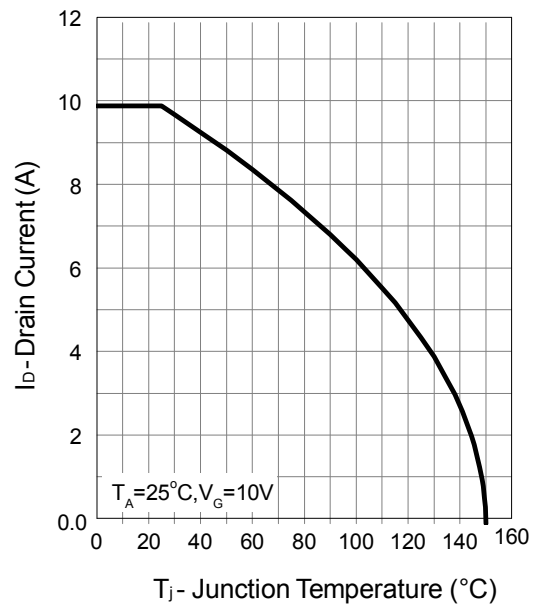
- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, $t < 10\text{sec}$.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.1\text{mH}, I_{AS}=-11A$
- 4.The power dissipation is limited by 150°C junction temperature
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N-Channel Typical Characteristics

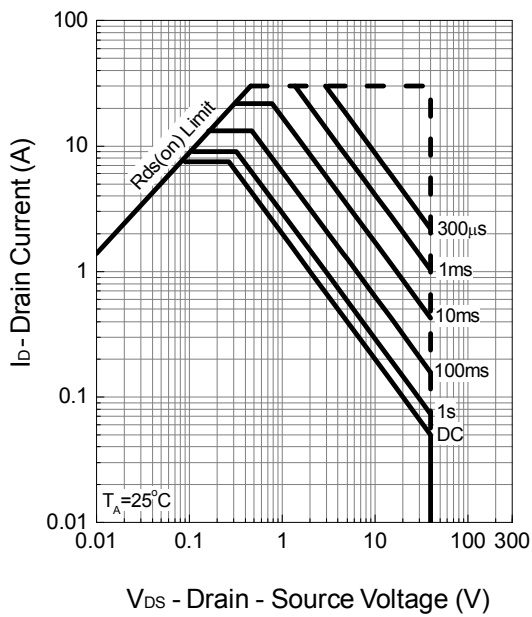
Power Dissipation



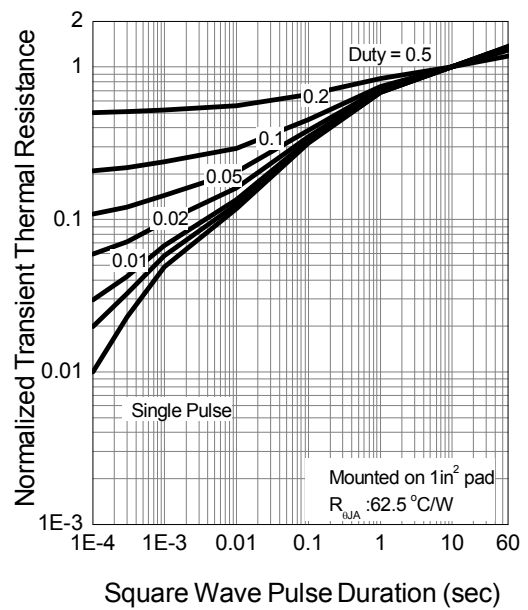
Drain Current



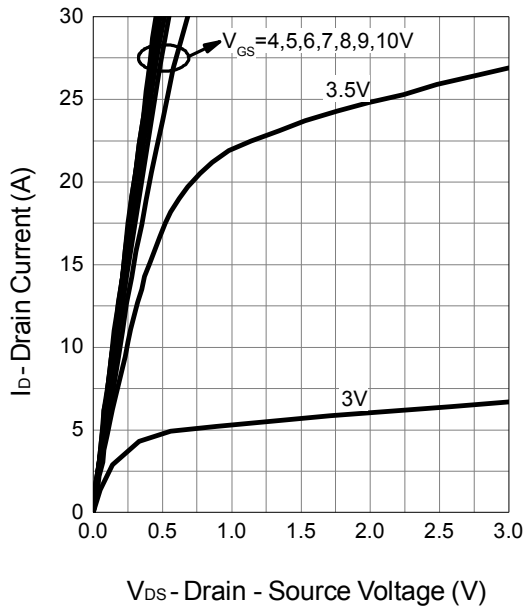
Safe Operation Area



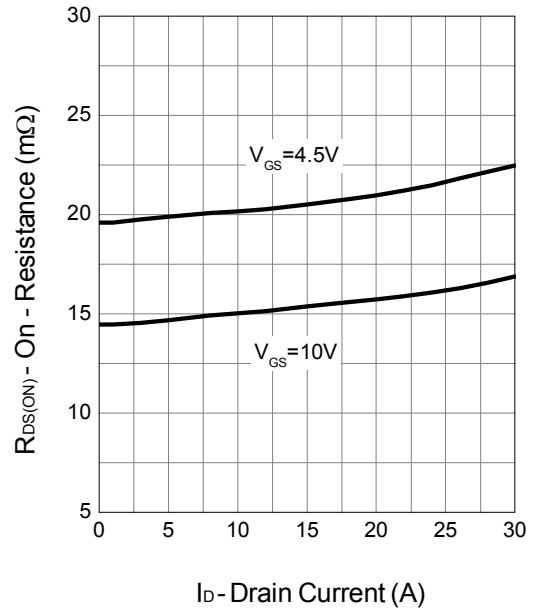
Thermal Transient Impedance



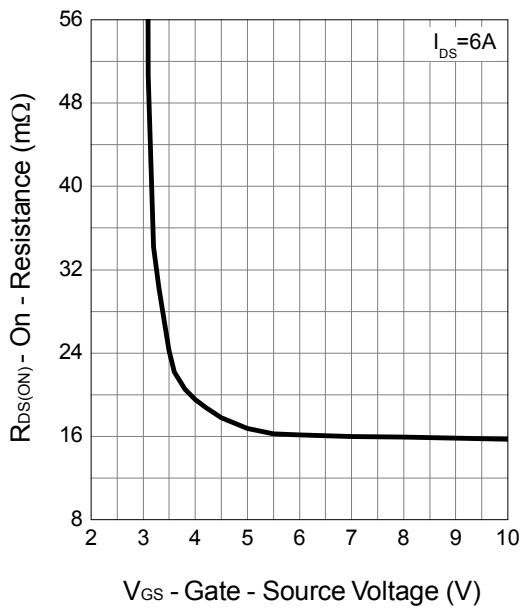
Output Characteristics



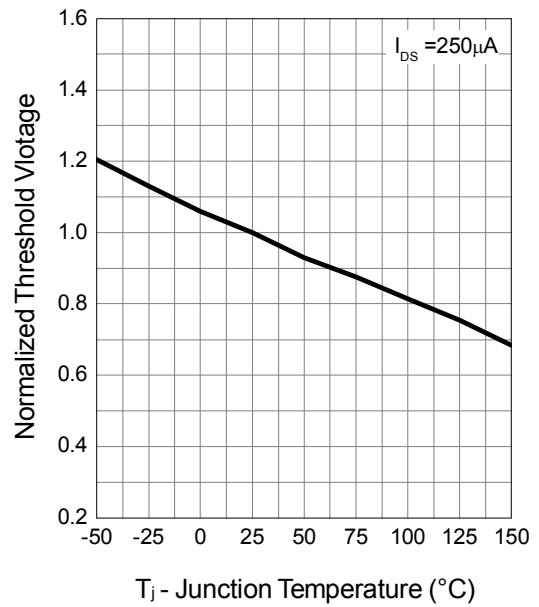
Drain-Source On Resistance



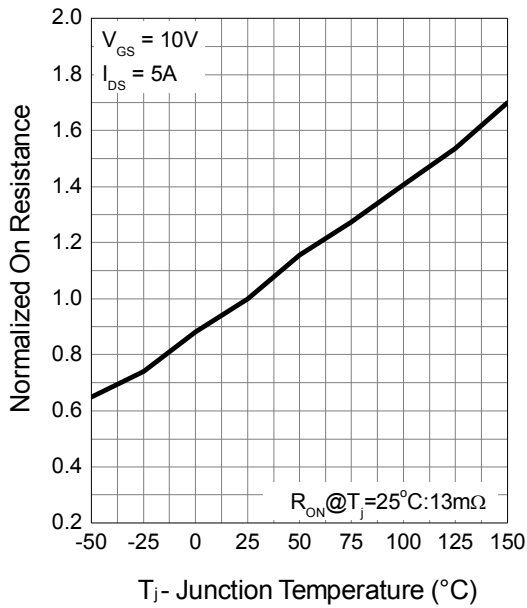
Gate-Source On Resistance



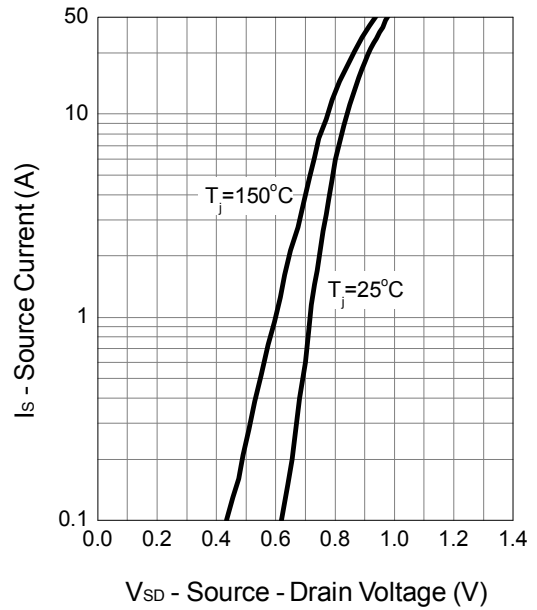
Gate Threshold Voltage



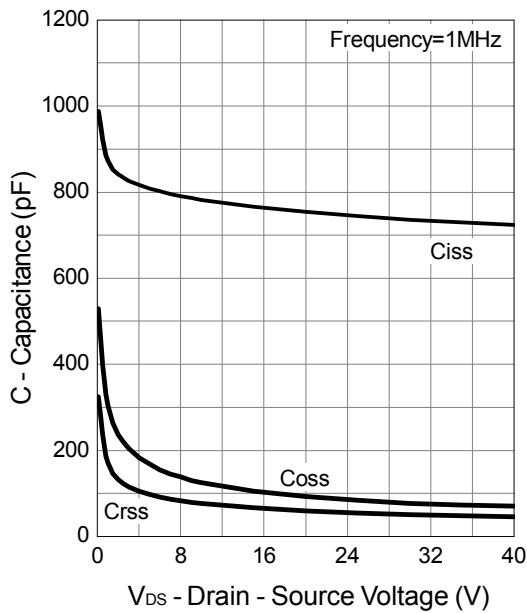
Drain-Source On Resistance



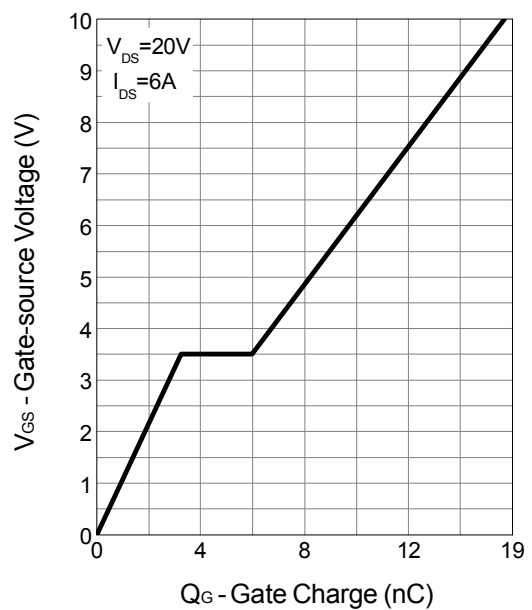
Source-Drain Diode Forward



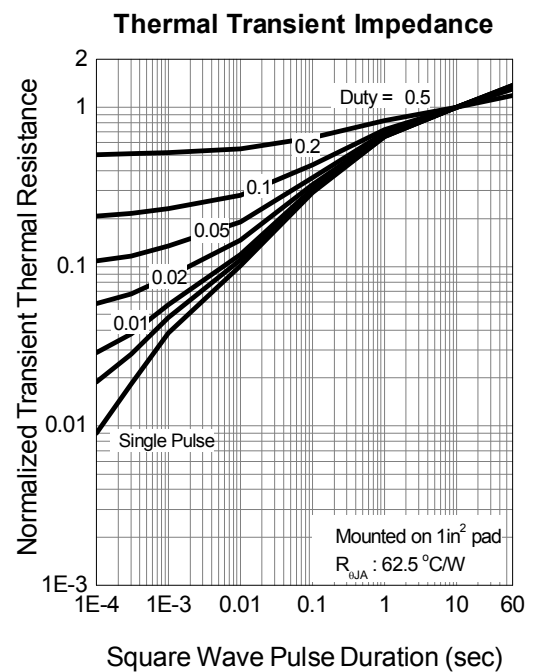
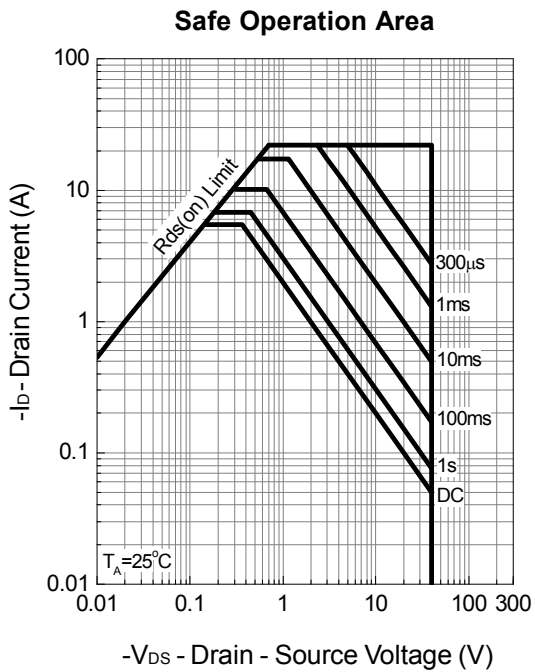
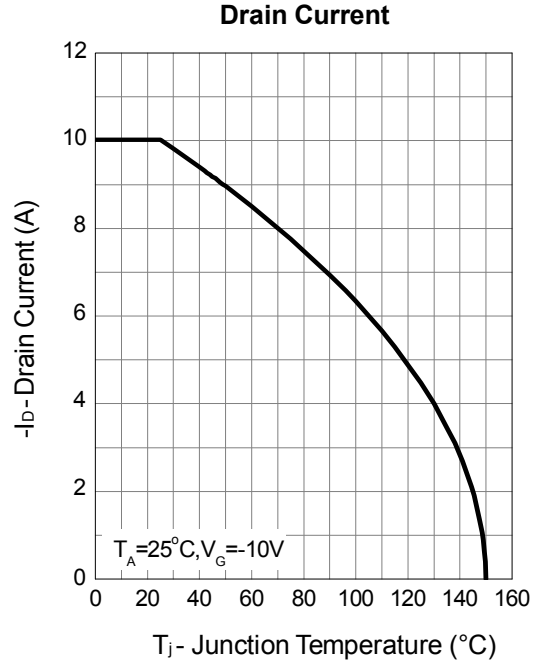
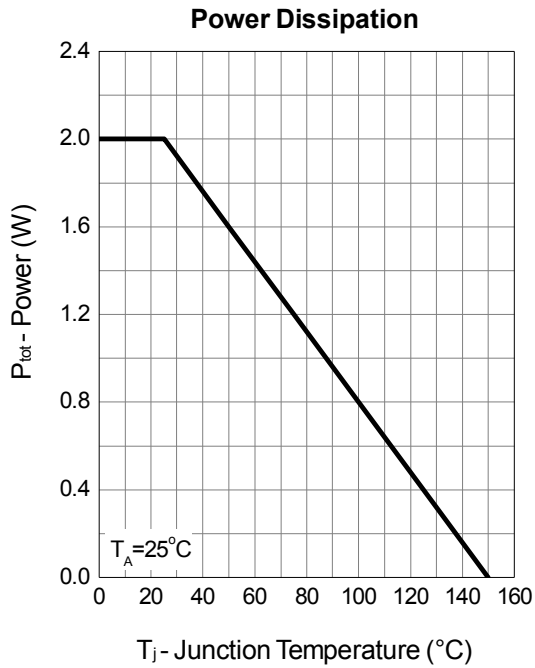
Capacitance



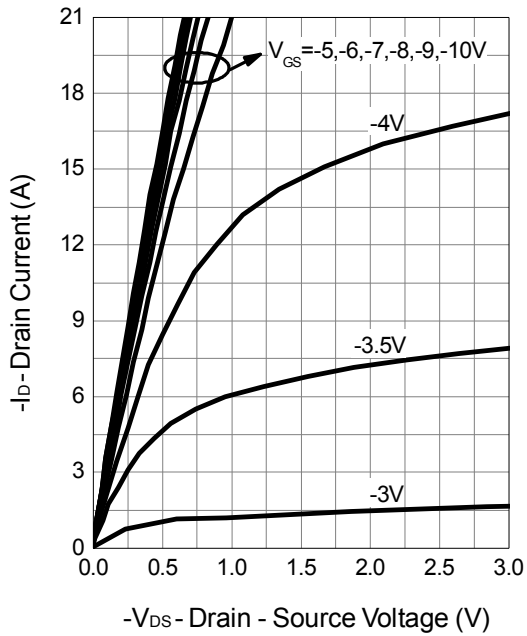
Gate Charge



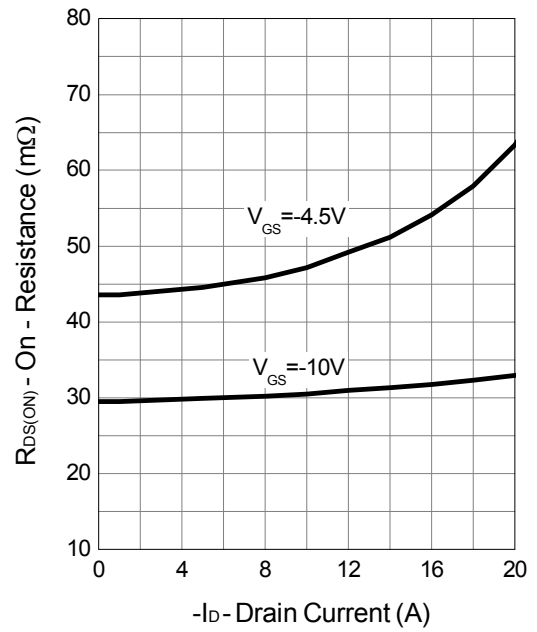
P-Channel Typical Characteristics



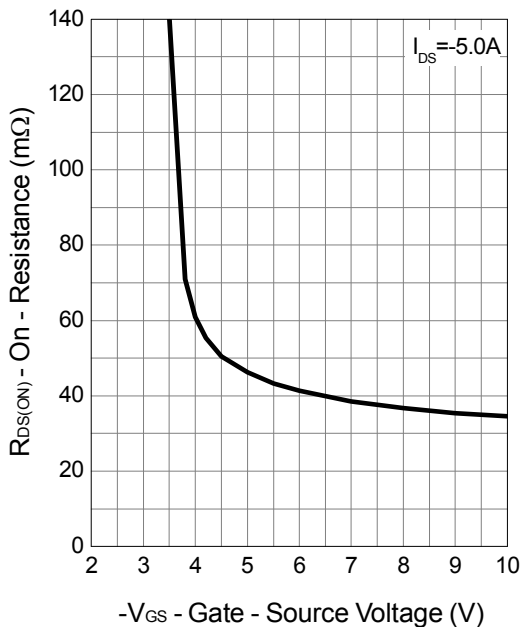
Output Characteristics



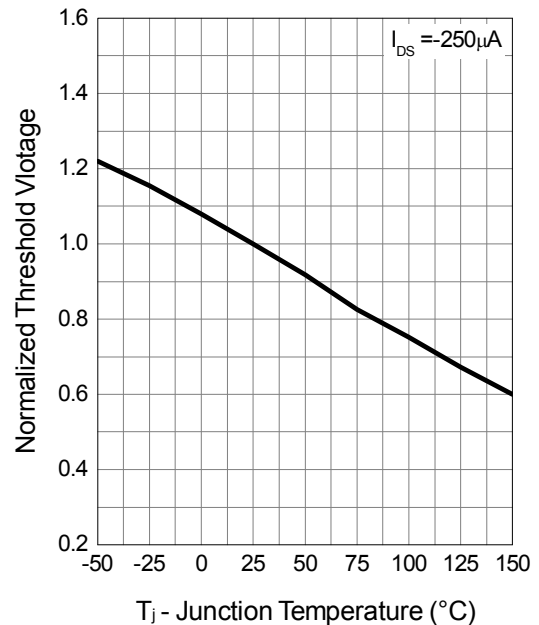
Drain-Source On Resistance



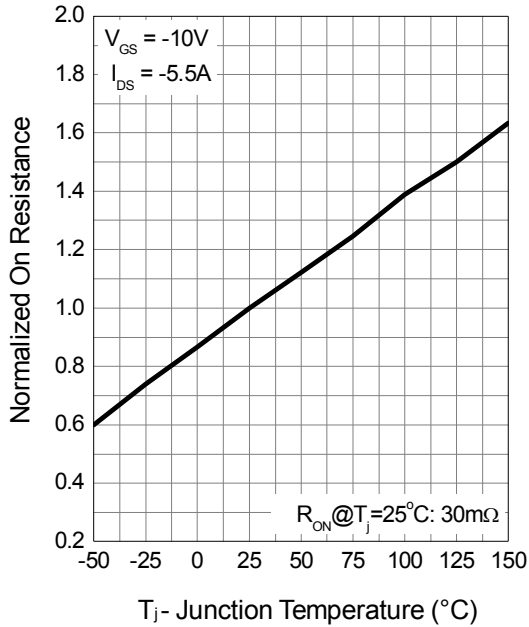
Gate-Source On Resistance



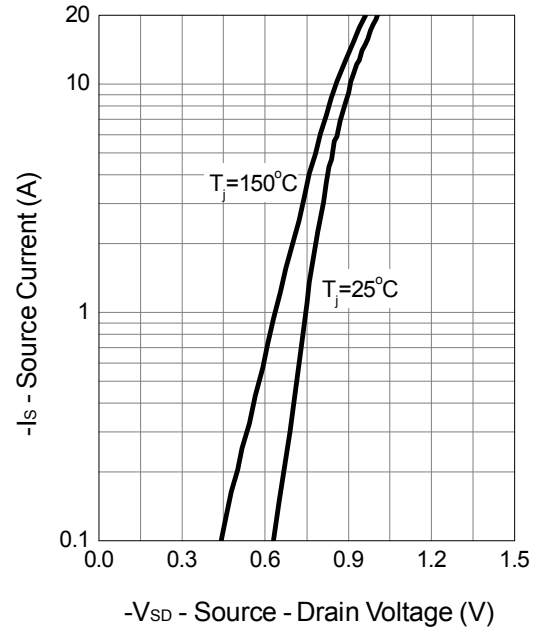
Gate Threshold Voltage



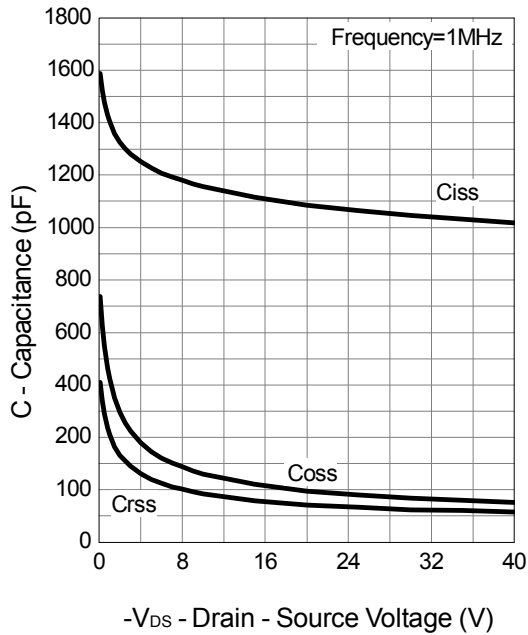
Drain-Source On Resistance



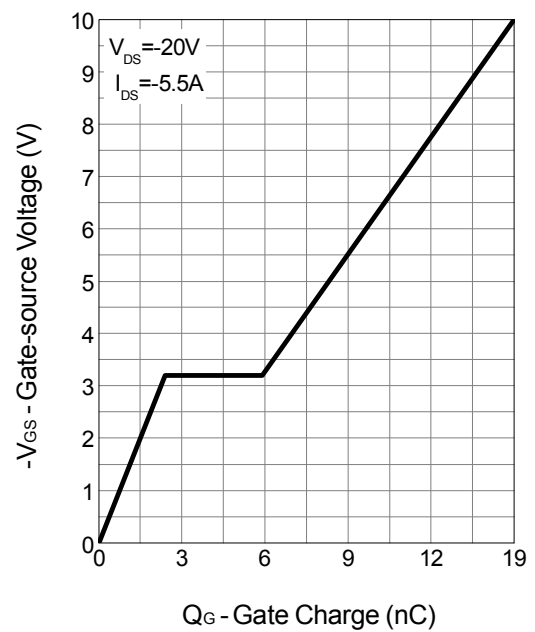
Source-Drain Diode Forward



Capacitance



Gate Charge





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